

MOSFET – N-Channel, POWERTRENCH®

100 V, 57 A, 16 mΩ

FDI150N10

Description

This N-Channel MOSFET is produced using onsemi's advanced POWERTRENCH process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Features

- $R_{DS(on)} = 12 \text{ m}\Omega$ (Typ.) @ $V_{GS} = 10 \text{ V}$, $I_D = 49 \text{ A}$
- Fast Switching Speed
- Low Gate Charge
- High Performance Trench Technology for Extremely Low $R_{DS(on)}$
- High Power and Current Handling Capability
- RoHS Compliant

Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- Battery Protection Circuit
- Motor Drives and Uninterruptible Power Supplies
- Micor Solar Inverter

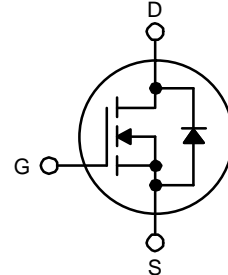
MOSFET MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	FDI150N10	Unit
V_{DSS}	Drain to Source Voltage	100	V
V_{GSS}	Gate to Source Voltage	± 20	V
I_D	Drain Current	– Continuous ($T_C = 25^\circ\text{C}$)	57 A
		– Continuous ($T_C = 100^\circ\text{C}$)	40 A
I_{DM}	Drain Current	– Pulsed (Note 1)	228 A
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	132	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	7.5	V/ns
P_D	Power Dissipation	($T_C = 25^\circ\text{C}$)	110 W
		– Derate Above 25°C	0.88 W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to $+150$	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

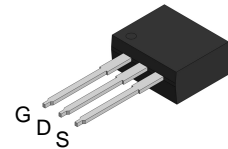
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. $L = 0.11 \text{ mH}$, $I_{AS} = 49 \text{ A}$, $V_{DD} = 50 \text{ V}$, $R_G = 25 \Omega$, starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 49 \text{ A}$, $di/dt \leq 200 \text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.

V_{DSS}	$R_{DS(on)} \text{ MAX}$	$I_D \text{ MAX}$
100 V	16 mΩ @ 10 V	57 A

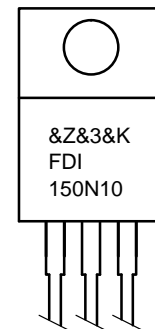


P-Channel MOSFET



I2PAK
CASE 418AV

MARKING DIAGRAM



- &Z = Assembly Plant Code
- &3 = 3-Digit Plant Code
- &K = 2-Digits Lot Run Traceability Code
- FDI150N10 = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping
FDI150N10	I2PAK	800 Units / Tube

FDI150N10

THERMAL CHARACTERISTICS

Symbol	Parameter	FDI150N10	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	1.13	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
--------	-----------	-----------------	-----	-----	-----	------

OFF CHARACTERISTICS

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu\text{A}$, $V_{GS} = 0 \text{ V}$, $T_C = 25^\circ\text{C}$	100	–	–	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C	–	0.1	–	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 100 \text{ V}$, $V_{GS} = 0 \text{ V}$	–	–	1	μA
		$V_{DS} = 100 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_C = 150^\circ\text{C}$	–	–	500	
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0 \text{ V}$	–	–	± 100	nA

ON CHARACTERISTICS

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250 \mu\text{A}$	2.5	–	4.5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}$, $I_D = 49 \text{ A}$	–	12	16	m Ω
g_{FS}	Forward Transconductance	$V_{DS} = 20 \text{ V}$, $I_D = 49 \text{ A}$	–	156	–	S

DYNAMIC CHARACTERISTICS

C_{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$	–	3580	4760	pF
C_{oss}	Output Capacitance		–	340	450	pF
C_{rss}	Reverse Transfer Capacitance		–	140	210	pF

SWITCHING CHARACTERISTICS

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 50 \text{ V}$, $I_D = 49 \text{ A}$, $V_{GS} = 10 \text{ V}$, $R_G = 25 \Omega$ (Note 4)	–	47	104	ns
t_r	Turn-On Rise Time		–	164	338	ns
$t_{d(off)}$	Turn-Off Delay Time		–	86	182	ns
t_f	Turn-Off Fall Time		–	83	176	ns
$Q_{g(tot)}$	Total Gate Charge at 10 V	$V_{DS} = 80 \text{ V}$, $I_D = 49 \text{ A}$, $V_{GS} = 10 \text{ V}$ (Note 4)	–	53	69	nC
Q_{gs}	Gate to Source Gate Charge		–	19	–	nC
Q_{gd}	Gate to Drain "Miller" Charge		–	15	–	nC

DRAIN-SOURCE DIODE CHARACTERISTICS

I_S	Maximum Continuous Drain to Source Diode Forward Current	–	–	57	A	
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	–	–	228	A	
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}$, $I_{SD} = 49 \text{ A}$	–	–	1.3	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V}$, $I_{SD} = 49 \text{ A}$, $di_F/dt = 100 \text{ A}/\mu\text{s}$	–	41	–	ns
Q_{rr}	Reverse Recovery Charge		–	70	–	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature typical characteristics.

TYPICAL PERFORMANCE CHARACTERISTICS

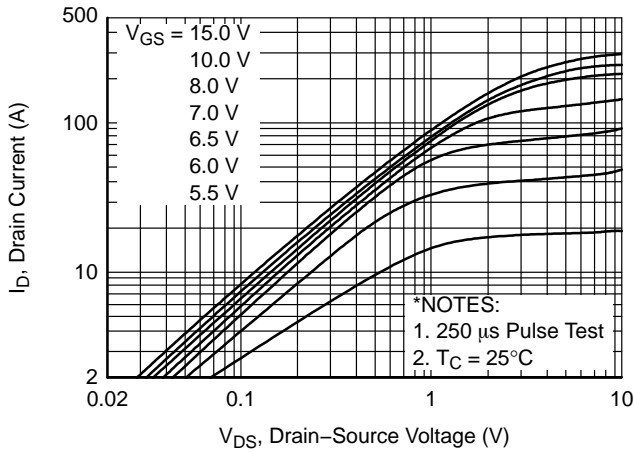


Figure 1. On-Region Characteristics

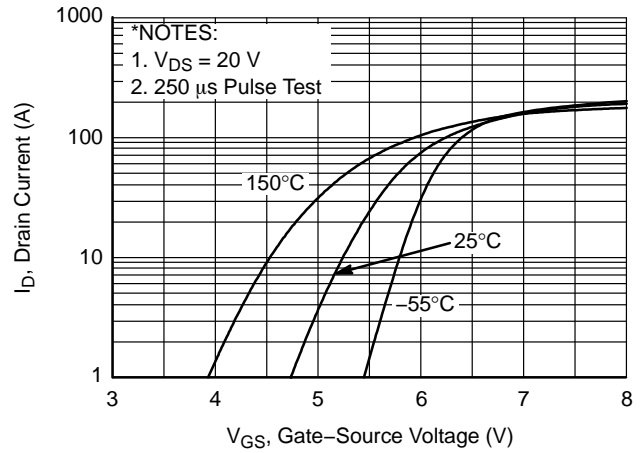


Figure 2. Transfer Characteristics

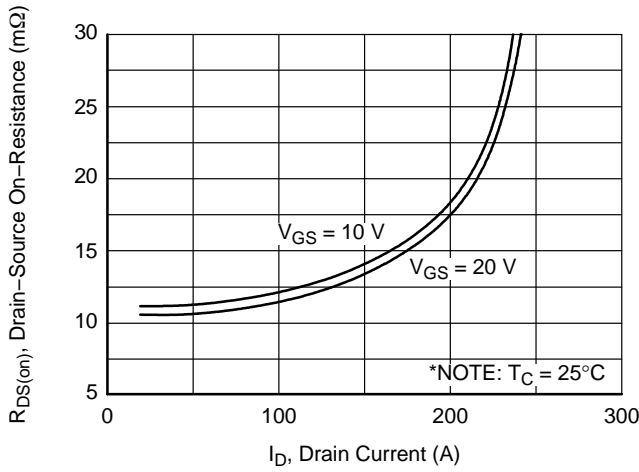


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

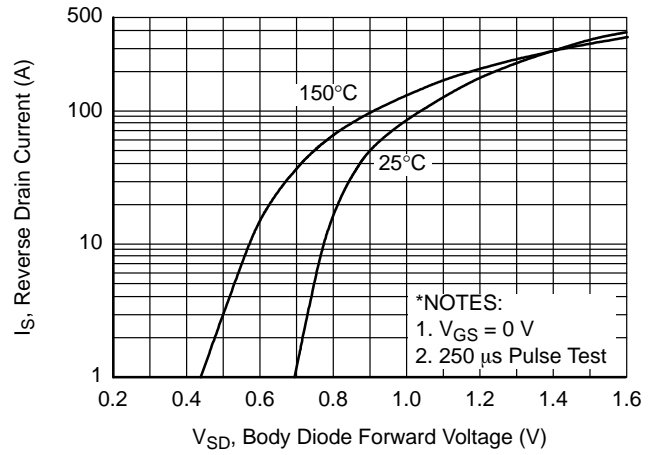


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

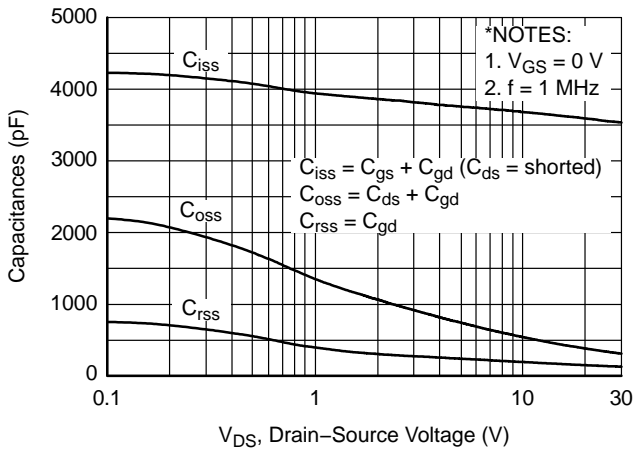


Figure 5. Capacitance Characteristics

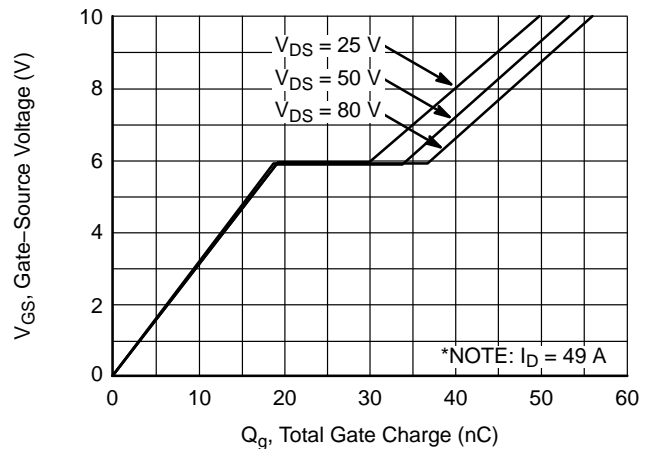


Figure 6. Gate Charge Characteristics

FDI150N10

TYPICAL PERFORMANCE CHARACTERISTICS (CONTINUED)

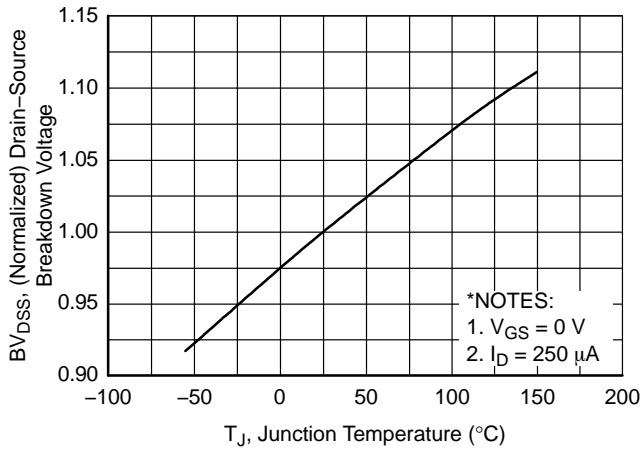


Figure 7. Breakdown Voltage Variation vs. Temperature

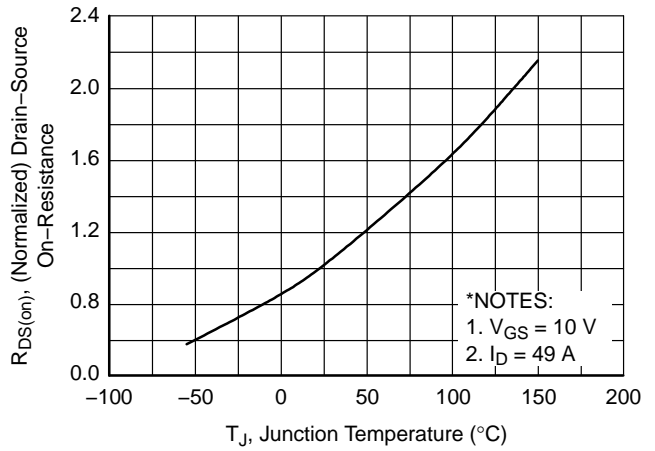


Figure 8. On-Resistance Variation vs. Temperature

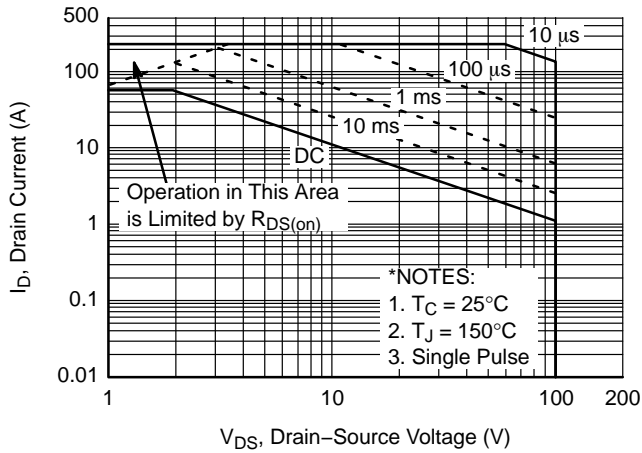


Figure 9. Maximum Safe Operating Area

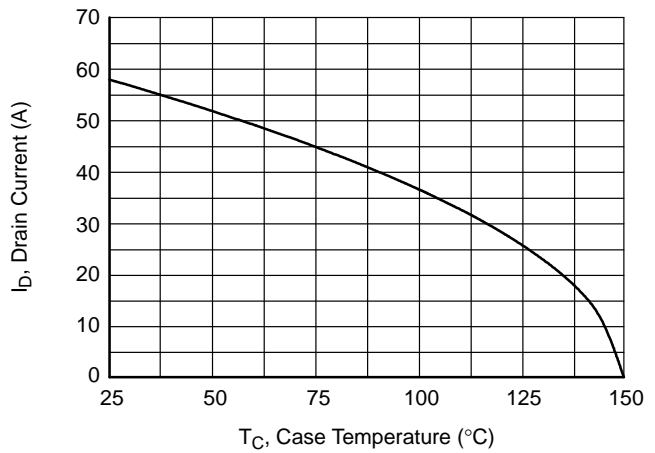


Figure 10. Maximum Drain Current vs. Case Temperature

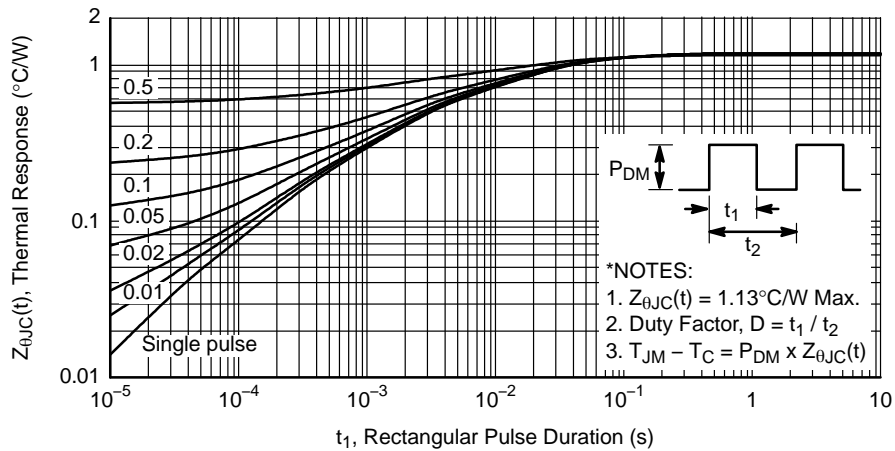


Figure 11. Transient Thermal Response Curve

FDI150N10

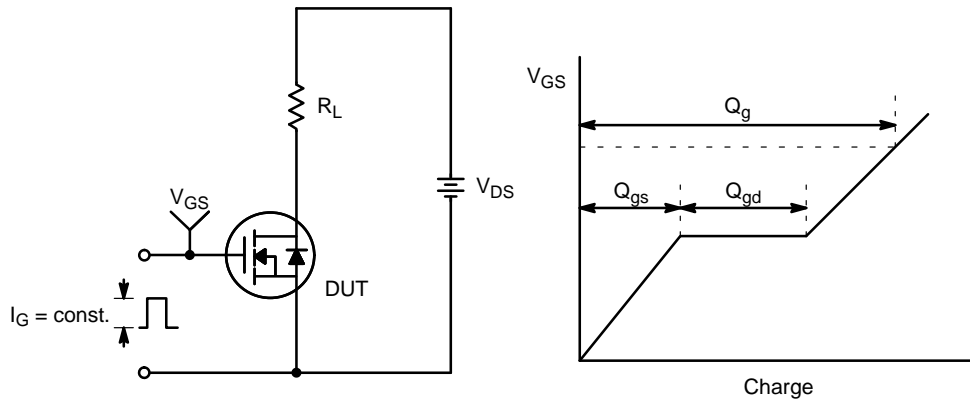


Figure 12. Gate Charge Test Circuit & Waveform

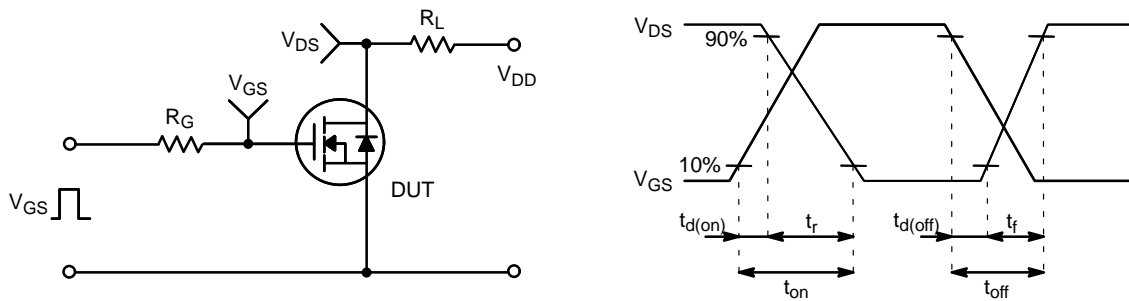


Figure 13. Resistive Switching Test Circuit & Waveforms

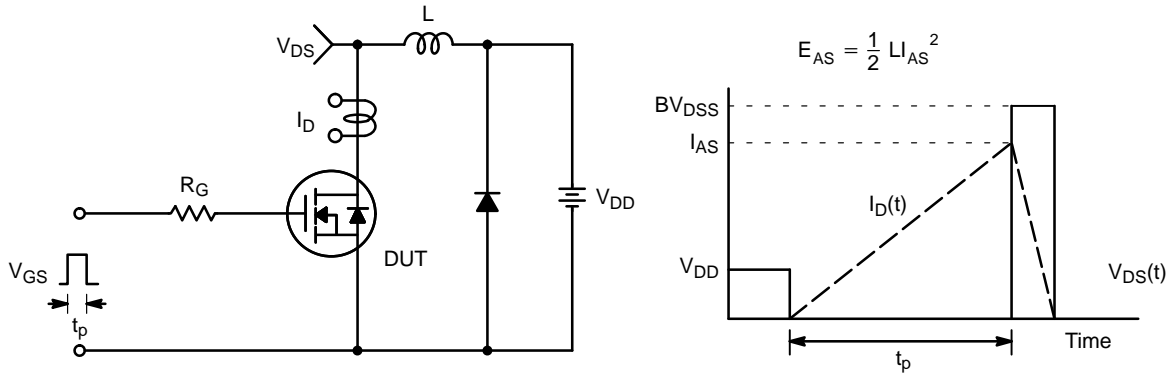


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

FDI150N10

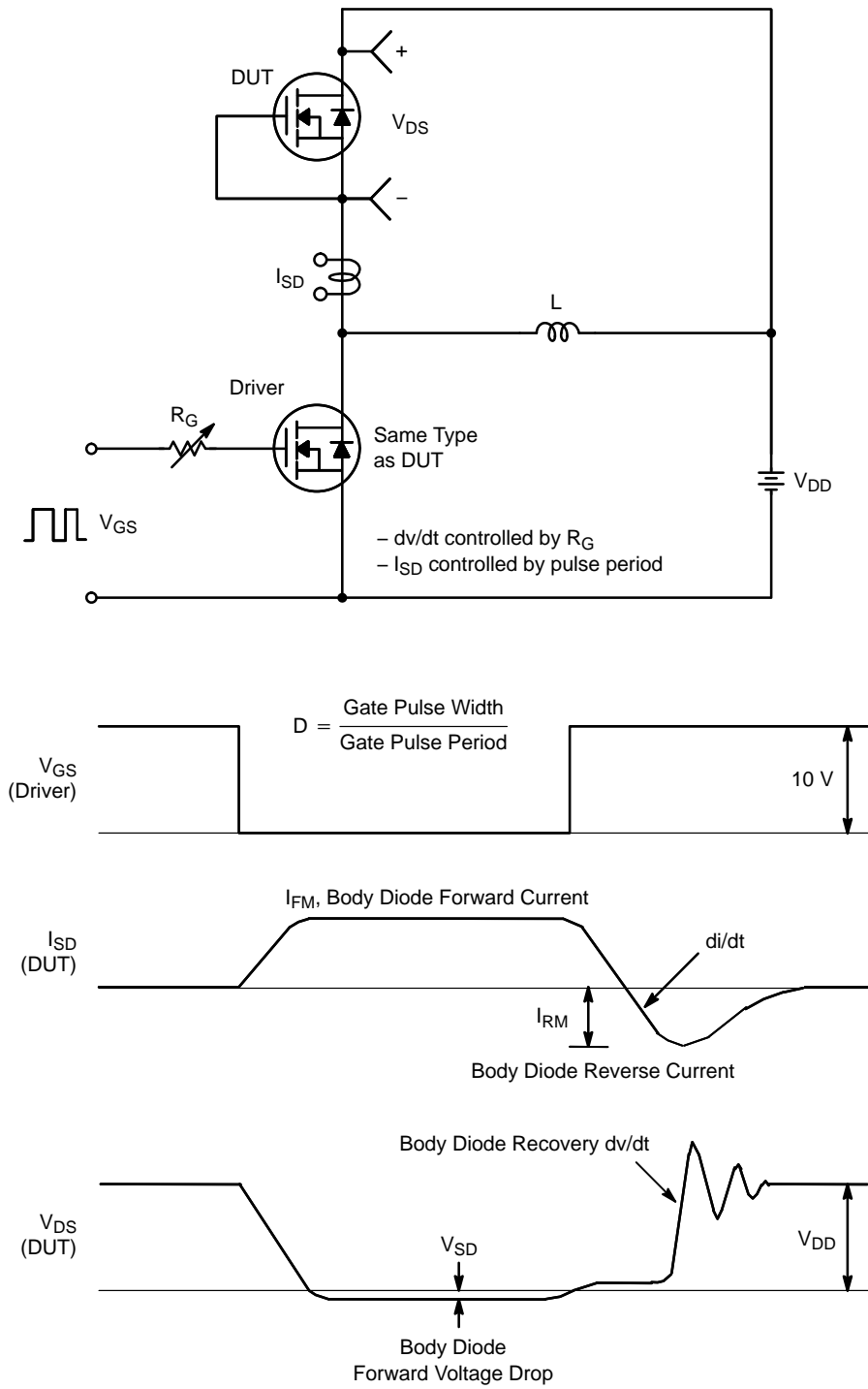


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales